

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

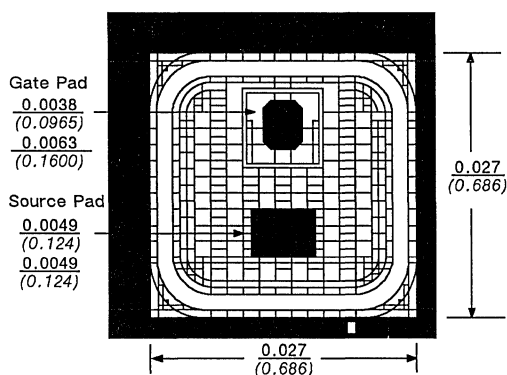
- Switching
- Amplification

FEATURES

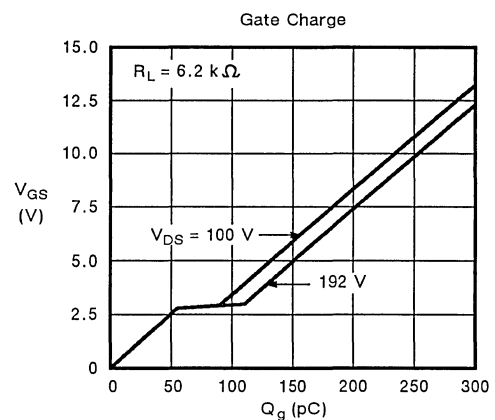
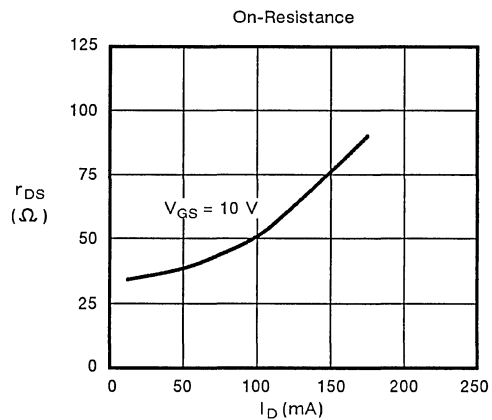
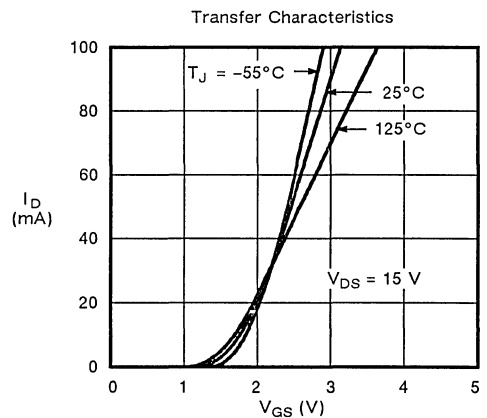
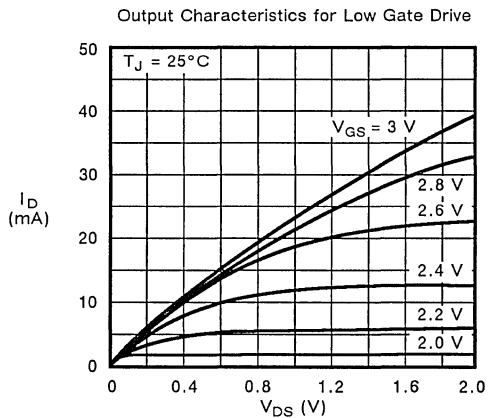
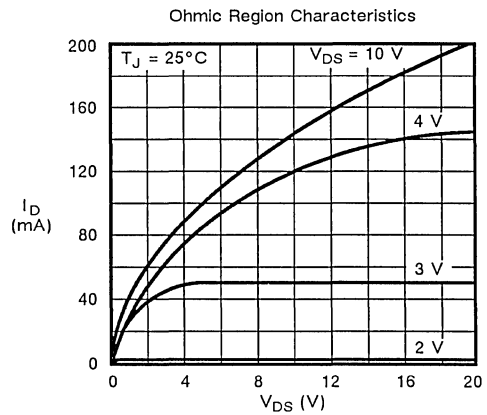
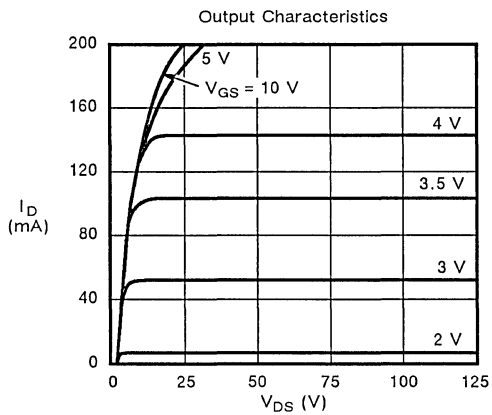
- High Breakdown > 240 V
- Available in Surface Mount SOT-23

TYPE	PACKAGE	DEVICE
Single	To-92	• 2N7007
	SOT-23	• 2N7001
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

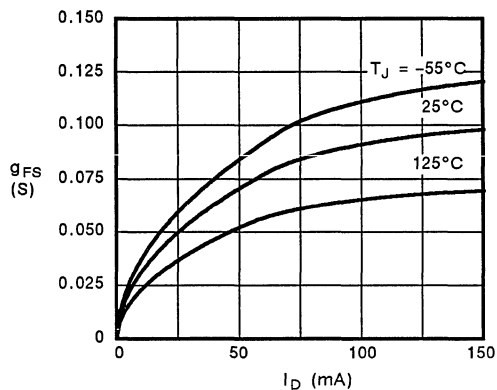


TYPICAL CHARACTERISTICS

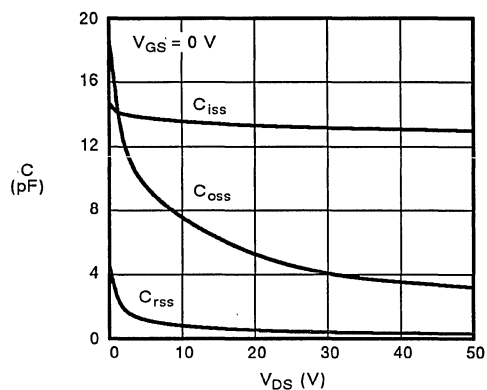


TYPICAL CHARACTERISTICS

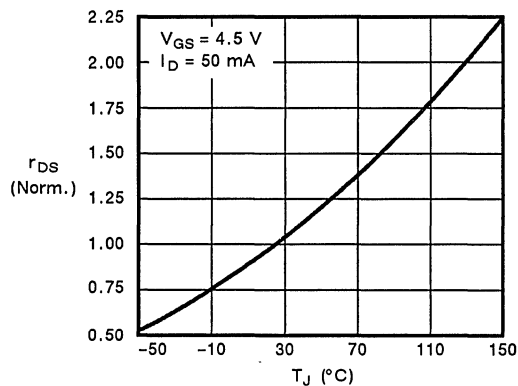
Transconductance



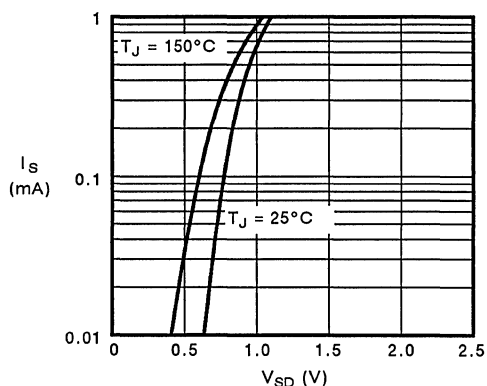
Capacitance



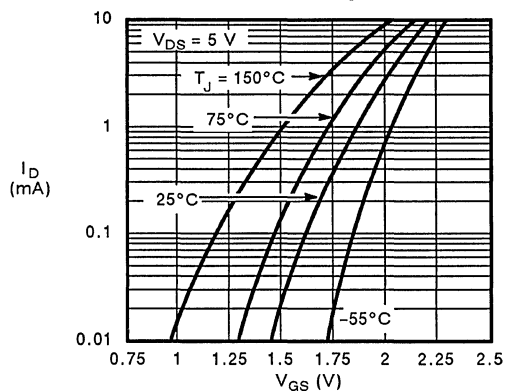
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

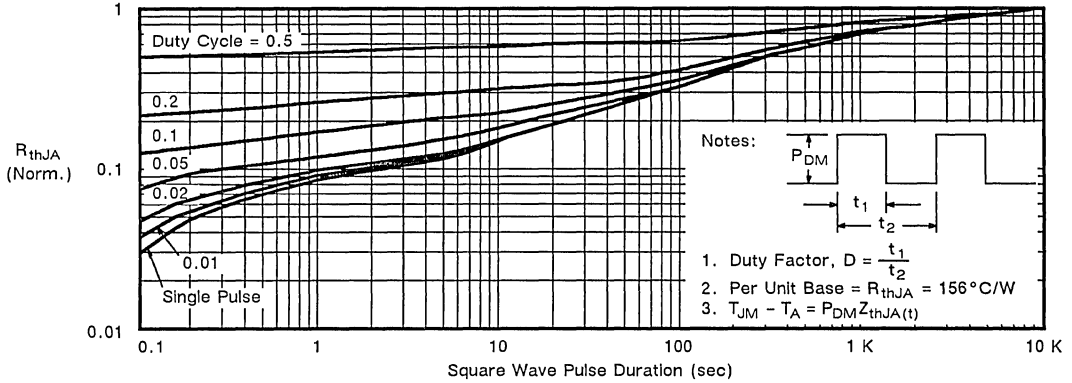


Threshold Region

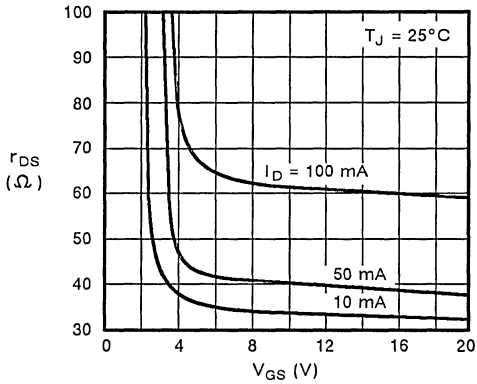


TYPICAL CHARACTERISTICS

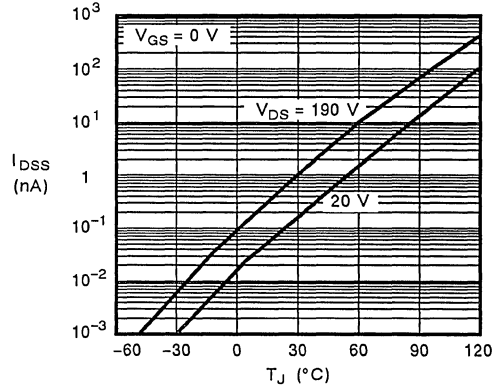
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



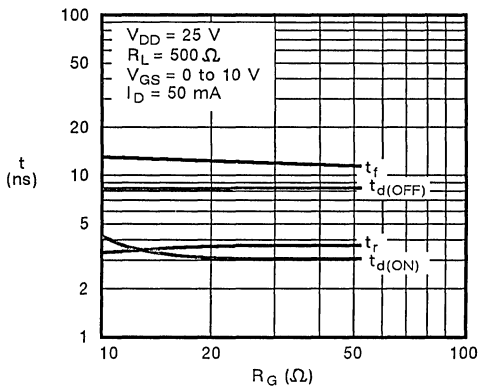
On-Resistance vs. Gate to Source Voltage



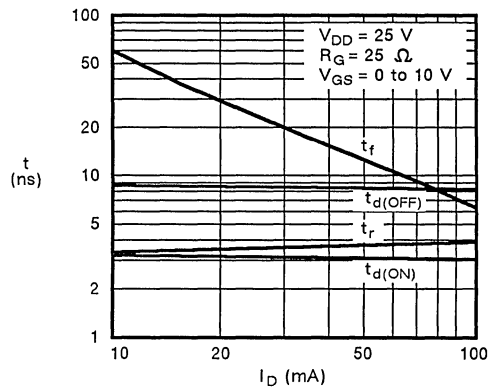
Off State Current



Drive Resistance Effects on Switching

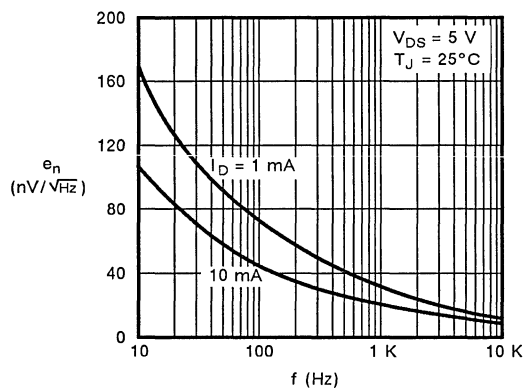


Load Condition Effects on Switching

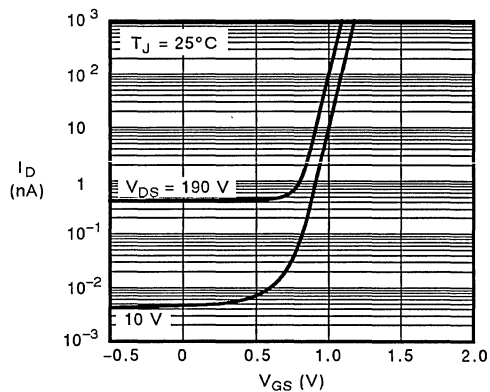


TYPICAL CHARACTERISTICS

Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current

